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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

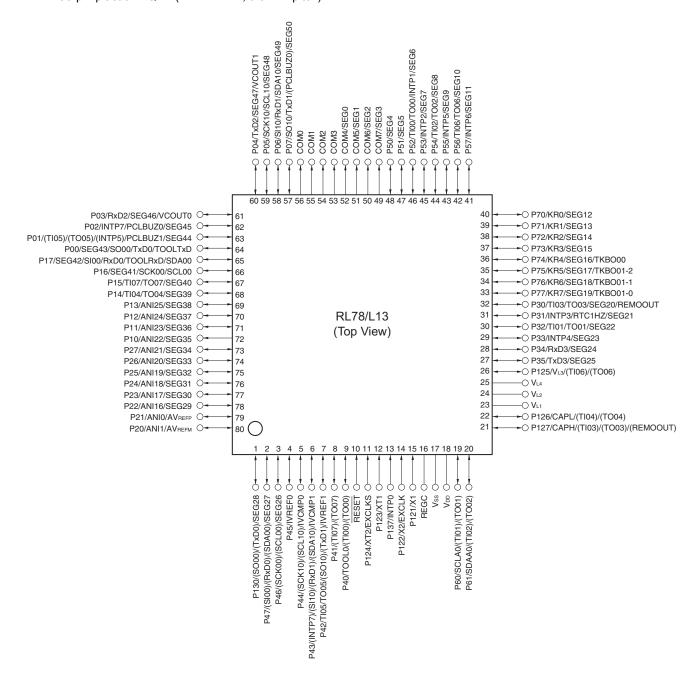
Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LCD, LVD, POR, PWM, WDT
Number of I/O	42
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 9x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10wlcgfb-30

RL78/L13 1. OUTLINE

<R> 1.3.2 80-pin products

- 80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)
- 80-pin plastic LFQFP (12 × 12 mm, 0.5 mm pitch)



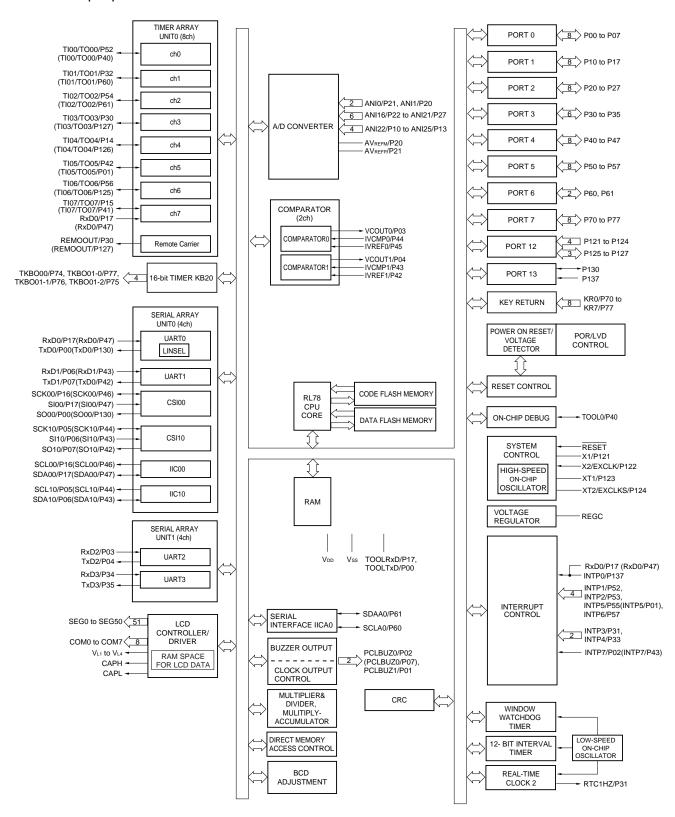
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/L13 User's Manual.

RL78/L13 1. OUTLINE

1.5.2 80-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/L13 User's Manual.

RL78/L13 1. OUTLINE

(2/2)

	Item	64-pin	80-pin				
		R5F10WLx (x = A, C-G)	R5F10WMx (x = A, C-G)				
Clock outp	ut/buzzer output controller	2					
		 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 (Main system clock: f_{Main} = 20 MHz operatio 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.09 (Subsystem clock: f_{SUB} = 32.768 kHz operation) 	n) 6 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz				
8/10-bit res	olution A/D converter	9 channels	12 channels				
Comparato	r	2 channels					
Serial inter	face	 [64-pin] CSI: 1 channel/UART (UART supporting LIN- CSI: 1 channel/UART: 1 channel/simplified I² UART: 1 channel 					
		CSI: 1 channel/UART (UART supporting LIN-	 [80-pin] CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I²C: 1 channel CSI: 1 channel/UART: 1 channel/simplified I²C: 1 channel UART: 2 channels 				
	I ² C bus	1 channel					
LCD contro	ller/driver	Internal voltage boosting method, capacitor sp method are switchable.	Internal voltage boosting method, capacitor split method, and external resistance division method are switchable.				
	Segment signal output	36 (32) ^{Note 1}	51 (47) ^{Note 1}				
	Common signal output	4 (8	Note 1				
Multiplier a	nd divider/multiply-	• 16 bits × 16 bits = 32 bits (Unsigned or signed)					
accumulato	or	• 32 bits ÷ 32 bits = 32 bits (Unsigned)					
		• 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed)					
DMA contro	oller	4 channels					
Vectored	Internal	32	35				
interrupt so	urces External	11	11				
Key interru	pt	5	8				
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction executionNote 2 Internal reset by RAM parity error Internal reset by illegal-memory access					
Power-on-r	eset circuit	Power-on-reset: 1.51 V (TYP.) Power-down-reset: 1.50 V (TYP.)					
Voltage detector		 Rising edge: 1.67 V to 4.06 V (14 steps) Falling edge: 1.63 V to 3.98 V (14 steps) 					
On-chip de	bug function	Provided					
Power sup	oly voltage	V _{DD} = 1.6 to 5.5 V (TA = -40 to +85°C)					
		V _{DD} = 2.4 to 5.5 V (TA = -40 to +105°C)					
Operating a	ambient temperature	Consumer applications: $T_A = -40 \text{ to } +85^{\circ}\text{C}$ Industrial applications: $T_A = -40 \text{ to } +105^{\circ}\text{C}$					

- **Notes 1.** The values in parentheses are the number of signal outputs when 8 com is used.
 - This reset occurs when instruction code FFH is executed.
 This reset does not occur during emulation using an in-circuit emulator or an on-chip debugging emulator.

2. ELECTRICAL SPECIFICATIONS ($T_A = -40 \text{ to } +85^{\circ}\text{C}$)

Target products A: Consumer applications; $T_A = -40 \text{ to } +85^{\circ}\text{C}$

R5F10WLAAFA, R5F10WLCAFA, R5F10WLDAFA, R5F10WLEAFA, R5F10WLFAFA, R5F10WLGAFA, R5F10WLAAFB, R5F10WLCAFB, R5F10WLDAFB, R5F10WLEAFB, R5F10WLFAFB, R5F10WMDAFA, R5F10WMAAFA, R5F10WMCAFA, R5F10WMGAFA, R5F10WMAAFB, R5F10WMCAFB, R5F10WMDAFB, R5F10WMBAFB, R5F10WMBAFB, R5F10WMBAFB, R5F10WMBAFB, R5F10WMBAFB

G: Industrial applications; when using T_A = -40 to +105°C specification products at T_A = -40 to +85°C R5F10WLAGFB, R5F10WLCGFB, R5F10WLDGFB, R5F10WLEGFB, R5F10WLEGFB, R5F10WLGGFB R5F10WMAGFB, R5F10WMCGFB, R5F10WMDGFB, R5F10WMEGFB, R5F10WMEGFB, R5F10WMEGFB, R5F10WMEGFB

- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. The pins mounted depend on the product. See 2.1 Port Function to 2.2.1 With functions for each product in the RL78/L13 User's Manual.

2.2 Oscillator Characteristics

2.2.1 X1 and XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) ^{Note}	Ceramic resonator/ crystal resonator	$2.7~V \leq V_{DD} \leq 5.5~V$	1.0		20.0	MHz
		$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	1.0		16.0	
		1.8 V ≤ V _{DD} < 2.4 V	1.0		8.0	
		1.6 V ≤ V _{DD} < 1.8 V	1.0		4.0	
XT1 clock oscillation frequency (fxT) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, see **5.4 System Clock Oscillator** in the RL78/L13 User's Manual.

2.2.2 On-chip oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions			TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Notes 1, 2}	fıн			1		24	MHz
High-speed on-chip oscillator clock frequency accuracy		–20 to +85°C	$1.8~V \leq V_{DD} \leq 5.5~V$	-1.0		+1.0	%
			1.6 V ≤ V _{DD} < 1.8 V	-5.0		+5.0	%
		–40 to –20°C	$1.8~V \leq V_{DD} \leq 5.5~V$	-1.5		+1.5	%
			1.6 V ≤ V _{DD} < 1.8 V	-5.5		+5.5	%
Low-speed on-chip oscillator clock frequency	fiL				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

- **Notes 1.** The high-speed on-chip oscillator frequency is selected by bits 0 to 4 of the option byte (000C2H/010C2H) and bits 0 to 2 of the HOCODIV register.
 - 2. This indicates the oscillator characteristics only. Refer to **AC Characteristics** for the instruction execution time.



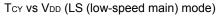
- Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the LCD controller/driver, A/D converter, LVD circuit, comparator, I/O port, on-chip pull-up/pull-down resistors, and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When setting ultra-low power consumption oscillation (AMPHS1 = 1). The current flowing into the LCD controller/driver, 16-bit timer KB20, real-time clock 2, 12-bit interval timer, and watchdog timer is not included.
 - 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

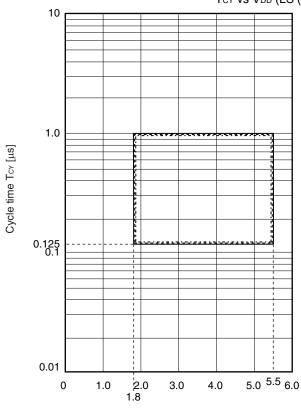
HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @1 \text{ MHz}$ to 24 MHz

 $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V@1 MHz to 16 MHz}$

LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} \textcircled{2}1 \text{ MHz}$ to 8 MHz LV (low-voltage main) mode: $1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} \textcircled{2}1 \text{ MHz}$ to 4 MHz

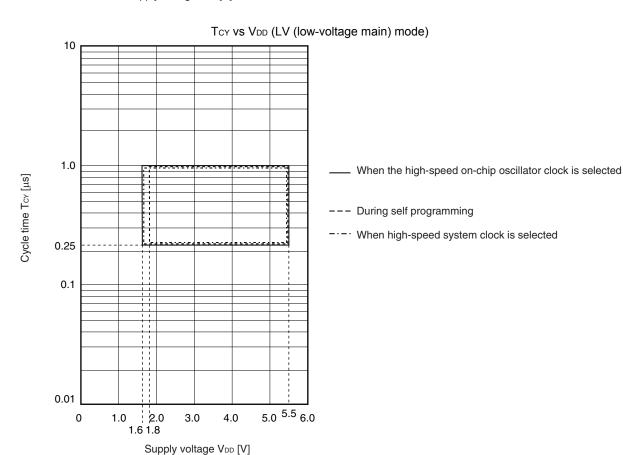
- **Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fHOCO: High-speed on-chip oscillator clock frequency (48 MHz max.)
 - 3. fil: High-speed on-chip oscillator clock frequency (24 MHz max.)
 - 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C



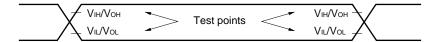


- --- When the high-speed on-chip oscillator clock is selected
- --- During self programming
- --- When high-speed system clock is selected

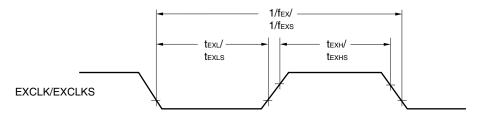
Supply voltage VDD [V]



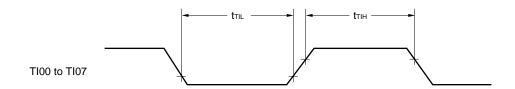
AC Timing Test Points

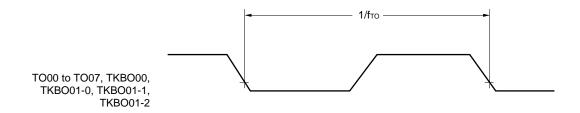


External System Clock Timing

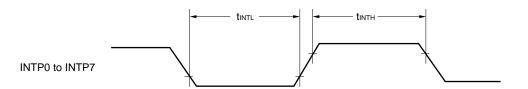


TI/TO Timing



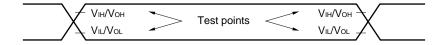


Interrupt Request Input Timing



2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		h-speed Mode	,	/-speed Mode	`	/-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate ^{Note}		$2.4 \ \text{V} \le \text{V}_{\text{DD}} \le 5.5 \ \text{V}$		fмск/6		fмск/6		fмск/6	bps
1		Theoretical value of the maximum transfer rate fmck = fclk Note 2		4.0		1.3		0.6	Mbps
		1.8 V ≤ V _{DD} ≤ 5.5 V		_		fмск/6		fмск/6	bps
		Theoretical value of the maximum transfer rate fmck = fcLk ^{Note 2}		-		1.3		0.6	Mbps
		1.6 V ≤ V _{DD} ≤ 5.5 V		_		-		fмск/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 2		_		-		0.6	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

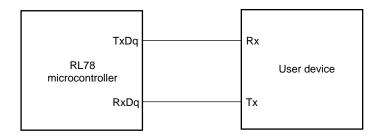
HS (high-speed main) mode: 24 MHz (2.7 V \leq V_{DD} \leq 5.5 V)

16 MHz (2.4 V \leq V_{DD} \leq 5.5 V)

LS (low-speed main) mode: 8 MHz (1.8 V \leq VDD \leq 5.5 V) LV (low-voltage main) mode: 4 MHz (1.6 V \leq VDD \leq 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage Input channel	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = V _{DD} Reference voltage (-) = Vss	Reference voltage (+) = V _{BGR} Reference voltage (-) = AV _{REFM}
ANIO, ANI1	_	See 2.6.1 (2).	See 2.6.1 (3).
ANI16 to ANI25	See 2.6.1 (1) .		
Internal reference voltage Temperature sensor output	See 2.6.1 (1) .		_
voltage			

(1) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pins: ANI16 to ANI25, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{REFP}, \text{Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V})$

Parameter	Symbol	C	conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V		1.2	±5.0	LSB
		AV _{REFP} = V _{DD} Note 3	$1.6 \text{ V} \le \text{AV}_{\text{REFP}} \le 5.5 \text{ V}^{\text{Note 4}}$		1.2	±8.5	LSB
Conversion time	tconv	v 10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target pin:	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μs
		ANI16 to ANI25	$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μs
			$1.6~V \leq V_{DD} \leq 5.5~V$	57		95	μs
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μs
	reference voltage.		$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μs
		2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs	
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±0.35	%FSR
		AV _{REFP} = V _{DD} Note 3	$1.6~V \leq AV_{REFP} \leq 5.5~V^{\text{Note 4}}$			±0.60	%FSR
Full-scale errorNotes 1, 2	Ers	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±0.35	%FSR
		AV _{REFP} = V _{DD} Note 3	$1.6~V \leq AV_{REFP} \leq 5.5~V^{\text{Note 4}}$			±0.60	%FSR
Integral linearity errorNote 1	ILE	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±3.5	LSB
		AV _{REFP} = V _{DD} Note 3	$1.6~V \leq AV_{REFP} \leq 5.5~V^{\text{Note 4}}$			±6.0	LSB
Differential linearity errorNote 1	DLE	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±2.0	LSB
		AV _{REFP} = V _{DD} Note 3	$1.6~V \leq AV_{REFP} \leq 5.5~V^{\text{Note 4}}$			±2.5	LSB
Analog input voltage	VAIN	ANI16 to ANI25		0		AVREFP	V
	Internal reference volt (2.4 V ≤ V _{DD} ≤ 5.5 V, I		tage HS (high-speed main) mode))	V _{BGR} Note 5			V
		Temperature sensor of (2.4 V \leq V _{DD} \leq 5.5 V,	output voltage HS (high-speed main) mode))	V _{TMPS25} Note 5		V	

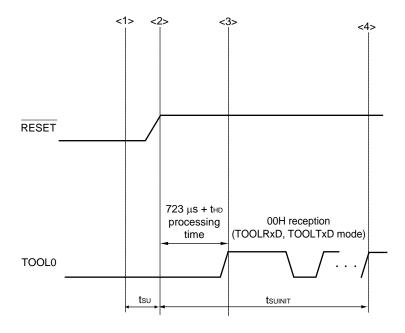
(Notes are listed on the next page.)



2.11 Timing Specifications for Switching Flash Memory Programming Modes

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tнo	POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and completion the baud rate setting.

Remark tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

tsu: Time to release the external reset after the TOOL0 pin is set to the low level

thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

"G: Industrial applications ($T_A = -40$ to +105°C) differ from "A: Consumer applications" in function as follows:

Fields of Application	A: Consumer applications	G: Industrial applications
Operating ambient temperature	T _A = -40 to +85°C	TA = -40 to +105°C
Operation mode operating voltage range	HS (high-speed main) mode: $2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V} \textcircled{0}1 \text{ MHz to } 24 \text{ MHz}$ $2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V} \textcircled{0}1 \text{ MHz to } 16 \text{ MHz}$ $LS \text{ (low-speed main) mode:}$ $1.8 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V} \textcircled{0}1 \text{ MHz to } 8 \text{ MHz}$ $LV \text{ (low-voltage main) mode:}$ $1.6 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V} \textcircled{0}1 \text{ MHz to } 4 \text{ MHz}$	HS (high-speed main) mode only: $2.7~V \le V_{DD} \le 5.5~V @ 1~MHz~to~24~MHz$ $2.4~V \le V_{DD} \le 5.5~V @ 1~MHz~to~16~MHz$
High-speed on-chip oscillator clock accuracy	1.8 V ≤ VDD ≤ 5.5 V: ±1.0 % @ TA = -20 to +85°C ±1.5 % @ TA = -40 to -20°C 1.6 V ≤ VDD < 1.8 V: ±5.0 % @ TA = -20 to +85°C ±5.5 % @ TA = -40 to -20°C	$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$: $\pm 2.0 \%$ @ $T_A = +85 \text{ to } +105^{\circ}\text{C}$ $\pm 1.0 \%$ @ $T_A = -20 \text{ to } +85^{\circ}\text{C}$ $\pm 1.5 \%$ @ $T_A = -40 \text{ to } -20^{\circ}\text{C}$
Serial array unit	UART CSI: fclk/2 (16 Mbps supported), fclk/4 Simplified I ² C	UART CSI: fclk/4 Simplified I ² C
IICA	Standard mode Fast mode Fast mode plus	Standard mode Fase mode
Voltage detector	• Rising: 1.67 V to 4.06 V (14 levels) • Falling: 1.63 V to 3.98 V (14 levels)	Rising: 2.61 V to 4.06 V (8 levels)Falling: 2.55 V to 3.98 V (8 levels)

Remark Electrical specifications of G: Industrial applications ($T_A = -40$ to $+105^{\circ}$ C) differ from "A: Consumer applications". For details, see **3.1** to **3.11** below.

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings (1/3)

Parameter	Symbol	Conditions	Ratings	
Supply voltage	V _{DD}		-0.5 to +6.5	V
REGC pin input voltage	Virego	REGC	-0.3 to +2.8 and -0.3 to V _{DD} +0.3 ^{Note 1}	V
Input voltage V ₁₁		P00 to P07, P10 to P17, P20 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P121 to P127, P130, P137	-0.3 to V _{DD} +0.3 ^{Note 2}	V
	V ₁₂	P60 and P61 (N-ch open-drain) EXCLK, EXCLKS, RESET	-0.3 to +6.5 -0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	Vo1	P00 to P07, P10 to P17, P20 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P121 to P127, P130, P137	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Analog input voltage	Val1	ANI0, ANI1, ANI16 to ANI26	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF(+)} +0.3 ^{Notes 2, 3}	V

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed $AV_{REF(+)} + 0.3 V$ in case of A/D conversion target pin.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - **2.** $AV_{REF (+)}$: + side reference voltage of the A/D converter.
 - 3. Vss: Reference voltage



Absolute Maximum Ratings (2/3)

Parameter	Symbol		Conditions	Ratings	Unit
LCD voltage	V _{L1}	V _{L1} voltage ^{Note 1}	V _{L1} voltage ^{Note 1} -0.3 to +2.8 and -0.3 to V _{L4} +0.3		
	V _{L2}	V _{L2} voltage ^{Note 1}		-0.3 to V _{L4} +0.3 ^{Note 2}	V
	V _{L3}	V _{L3} voltage ^{Note 1} -0.3		-0.3 to V _{L4} +0.3 ^{Note 2}	V
	V _{L4}	V _{L4} voltage ^{Note 1}		-0.3 to +6.5	V
	VLCAP	CAPL, CAPH volt	age ^{Note 1}	-0.3 to V _{L4} +0.3 ^{Note 2}	V
	Vouт	COM0 to COM7	External resistance division method	-0.3 to V_{DD} +0.3 $^{Note 2}$	V
		SEG0 to SEG50	Capacitor split method	-0.3 to V_{DD} +0.3 $^{Note 2}$	V
		output voltage	Internal voltage boosting method	-0.3 to V _{L4} +0.3 ^{Note 2}	V

- **Notes 1.** This value only indicates the absolute maximum ratings when applying voltage to the V_{L1}, V_{L2}, V_{L3}, and V_{L4} pins; it does not mean that applying voltage to these pins is recommended. When using the internal voltage boosting method or capacitance split method, connect these pins to Vss via a capacitor (0.47 μ F \pm 30%) and connect a capacitor (0.47 μ F \pm 30%) between the CAPL and CAPH pins.
 - 2. Must be 6.5 V or lower.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Vss: Reference voltage

<R>

3.3 DC Characteristics

3.3.1 Pin characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	Іон1	Per pin for P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130	2.4 V ≤ V _{DD} ≤ 5.5 V			-3.0 ^{Note 2}	mA
			$4.0~V \leq V_{DD} \leq 5.5~V$			-45.0	mA
			$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			-15.0	mA
	lон2	to P57, P70 to P77, P125 to P127, P130 (When duty = 70% ^{Note 3})	$2.4 \text{ V} \le \text{V}_{DD} \le 2.7 \text{ V}$			-7.0	mA
		Per pin for P20 and P21	$2.4~V \leq V_{DD} \leq 5.5~V$			-0.1 ^{Note 2}	mA
		Total of all pins (When duty = 70% ^{Note 3})	$2.4~V \leq V_{DD} \leq 5.5~V$			-0.2	mA

Notes 1. Value of the current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin

- 2. Do not exceed the total current value.
- 3. Output current value under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(loh \times 0.7)/(n \times 0.01)$

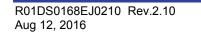
<Example> Where n = 80% and IoH = -45.0 mA

Total output current of pins = $(-45.0 \times 0.7)/(80 \times 0.01) = -39.375$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P04 to P07, P16, P17, P35, P42 to P44, P46, P47, P53 to P56, and P130 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.





 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130, P137	Normal input buffer	0.8V _{DD}		V _{DD}	>
	V _{IH2}	P03, P05, P06, P16, P17, P34, P43, P44, P46, P47, P53, P55	TTL input buffer $4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	2.2		V _{DD}	V
			TTL input buffer 3.3 V ≤ V _{DD} < 4.0 V	2.0		V _{DD}	V
			TTL input buffer 2.4 V ≤ V _{DD} < 3.3 V	1.5		V_{DD}	V
	V _{IH3}	P20, P21		0.7V _{DD}		V_{DD}	V
	V _{IH4}	P60, P61		0.7V _{DD}		6.0	V
	V _{IH5}	P121 to P124, P137, EXCLK, EXCLKS	s, RESET	0.8V _{DD}		V _{DD}	V
Input voltage, low	V _{IL1}	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130, P137	Normal input buffer	0		0.2V _{DD}	<
	V _{IL2}	P03, P05, P06, P16, P17, P34, P43, P44, P46, P47, P53, P55	TTL input buffer $4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	0		0.8	V
			TTL input buffer 3.3 V ≤ V _{DD} < 4.0 V	0		0.5	V
			TTL input buffer 2.4 V ≤ V _{DD} < 3.3 V	0		0.32	V
	V _{IL3}	P20, P21		0		0.3V _{DD}	V
	V _{IL4}	P60, P61		0		0.3V _{DD}	V
	V _{IL5}	P121 to P124, P137, EXCLK, EXCLKS	s, RESET	0		0.2V _{DD}	V

Caution The maximum value of V_{IH} of pins P00, P04 to P07, P16, P17, P35, P42 to P44, P46, P47, P53 to P56, and P130 is V_{DD}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



(4) During communication at same potential (simplified I²C mode)

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-speed	HS (high-speed main) Mode		
			MIN.	MAX.		
SCLr clock frequency	fscL	$2.7~V \leq V_{DD} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$		400 ^{Note 1}	kHz	
		2.4 V \leq V _{DD} \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ		100 ^{Note 1}	kHz	
Hold time when SCLr = "L"	tLOW	$2.7~V \leq V_{DD} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	1200		ns	
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 3 \text{ k}\Omega$	4600		ns	
Hold time when SCLr = "H"	tнісн	$2.7~V \leq V_{DD} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	1200		ns	
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 3 \text{ k}\Omega$	4600		ns	
Data setup time (reception)	tsu:DAT	$2.7~V \leq V_{DD} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	1/f _{MCK} + 220 ^{Note 2}		ns	
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 3 \text{ k}\Omega$	1/f _{MCK} + 580 ^{Note 2}		ns	
Data hold time (transmission)	thd:dat	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	0	770	ns	
		2.4 V \leq V _{DD} \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ	0	1420	ns	

Notes 1. The value must also be equal to or less than fmck/4.

2. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg).

(Remarks are listed on the next page.)



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/2) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high-speed	Unit	
					MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$ \begin{aligned} 4.0 & \ V \le V_{DD} \le 5.5 \ V, \\ 2.7 & \ V \le V_b \le 4.0 \ V, \\ C_b & = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	600		ns
			$ \begin{aligned} &2.7 \; V \leq V_{DD} < 4.0 \; V, \\ &2.3 \; V \leq V_b \leq 2.7 \; V, \\ &C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	1000		ns
			$2.4 \ V \leq V_{DD} < 3.3 \ V,$ $1.6 \ V \leq V_b \leq 1.8 \ V,$ $C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega$	2300		ns
SCKp high-level width	t кн1	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$	tkcy1/2 – 150		ns
		$2.7 \text{ V} \leq \text{V}_{DD} \leq C_b = 30 \text{ pF}, \text{ F}$	$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$	tксү1/2 - 340		ns
		2.4 V ≤ V _{DD} < C _b = 30 pF, F	$ = 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V}, $ $ = 5.5 \text{ k}Ω $	tkcy1/2 - 916		ns
SCKp low-level width	t _{KL1}	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $R_{\text{b}} = 1.4 \text{ k}\Omega$	tксү1/2 – 24		ns
		$2.7 \text{ V} \leq \text{V}_{DD} \leq \text{C}_{b} = 30 \text{ pF, F}$	$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}Ω$	tксү1/2 – 36		ns
		2.4 V ≤ V _{DD} < C _b = 30 pF, F	3.3 V , 1.6 V \leq V _b \leq 2.0 V, $R_b = 5.5 \text{ k}\Omega$	tkcy1/2 - 100		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsık1	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$	162		ns
		$2.7 \text{ V} \le \text{V}_{DD} \le \text{C}_b = 30 \text{ pF}, \text{ F}$	$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$	354		ns
		$2.4 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$ 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V}, $ $ R_b = 5.5 \text{ k}Ω $	958		ns
SIp hold time (from SCKp↑) ^{Note 1}	t _{KSI1}	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V},$ $R_{b} = 1.4 \text{ k}\Omega$	38		ns
		$2.7 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$	38		ns
		$2.4 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V},$ $R_b = 5.5 \text{ k}\Omega$	38		ns
Delay time from SCKp↓ to SOp output ^{Note 1}	tkso1	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$		200	ns
		$2.7 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$		390	ns
		$2.4 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V},$ $R_b = 5.5 \text{ k}\Omega$		966	ns

(Note, ${\bf Caution}$ and ${\bf Remark}$ are listed on the next page.)



3.8 RAM Data Retention Characteristics

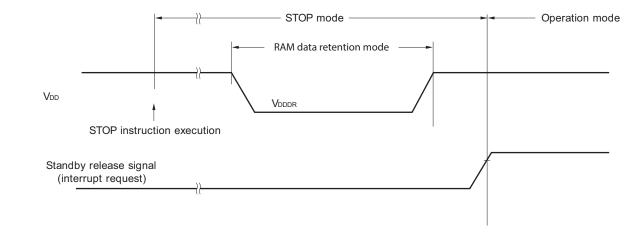
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$(T_A = -40 \text{ to } +105^{\circ}\text{C})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.44 ^{Note}		5.5	٧

<R> Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



3.9 Flash Memory Programming Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclk	2.4 V ≤ VDD ≤ 5.5 V	1		24	MHz
Number of code flash rewrites ^{Note 1, 2, 3}	Cerwr	Retained for 20 years TA = 85°C Note 4	1,000			Times
Number of data flash rewrites ^{Note 1, 2, 3}		Retained for 1 year TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C Note 4	100,000			
		Retained for 20 years TA = 85°C Note 4	10,000			

- **Notes 1.** 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
 - 2. When using flash memory programmer and Renesas Electronics self programming library
 - 3. This characteristic indicates the flash memory characteristic and based on Renesas Electronics reliability test.
 - **4.** This temperature is the average value at which data are retained.

Remark When updating data multiple times, use the flash memory as one for updating data.

3.10 Dedicated Flash Memory Programmer Communication (UART)

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps



Revision History

RL78/L13 Data Sheet

		Description			
Rev.	Date	Page	Summary		
0.01	Apr 13, 2012	-	First Edition issued		
0.02	Oct 31, 2012	-	Change of the number of segment pins		
			• 64-pin products: 36 pins		
			• 80-pin products: 51 pins		
2.10	Aug 12, 2016	1	Modification of features of 16-bit timer and 16-bit timer KB20 (IH) in 1.1 Features		
		5	Addition of product name (RL78/L13) and description (Top View) in 1.3.1 64-pin products		
		6	Addition of product name (RL78/L13) and description (Top View) in 1.3.2 80-pin products		
		10	Modification of functional overview of main system clock in 1.6 Outline of Functions		
		15	Modification of description in Absolute Maximum Ratings (3/3)		
		17, 18	Modification of description in 2.3.1 Pin characteristics		
		38	Modification of remark 3 in 2.5.1 (4) During communication at same potential (simplified I ² C mode)		
		68	Modification of the title and note, and addition of caution in 2.8 RAM Data Retention Characteristics		
		70	Addition of Remark		
		74	Modification of description in Absolute Maximum Ratings (T _A = 25 °C) (3/3)		
		76	Modification of description in 3.3.1 Pin characteristics		
		95	Modification of remark 3 in 3.5.1 (4) During communication at same potential (simplified I ² C mode)		
		118	Modification of the title and note, and addition of caution in 3.8 RAM Data Retention Characteristics		

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